

## Fast Bridge Rectifier

### ■特征 Features

- $I_o$  1A
- $V_{RRM}$  100V~1000V
- 玻璃钝化芯片  
Glass passivated chip
- 耐正向浪涌电流能力高  
High surge forward current capability

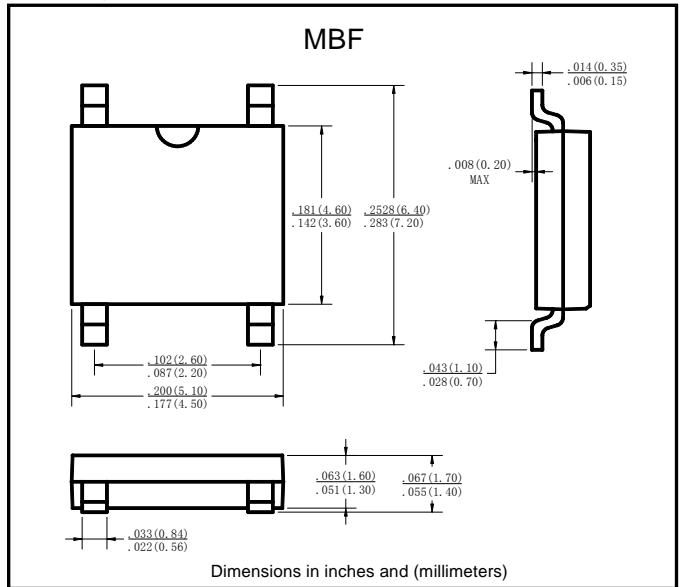
### ■用途 Applications

- 作一般电源单相桥式整流用  
General purpose 1 phase Bridge rectifier applications

### ■极限值 (绝对最大额定值)

#### Limiting Values (Absolute Maximum Rating)

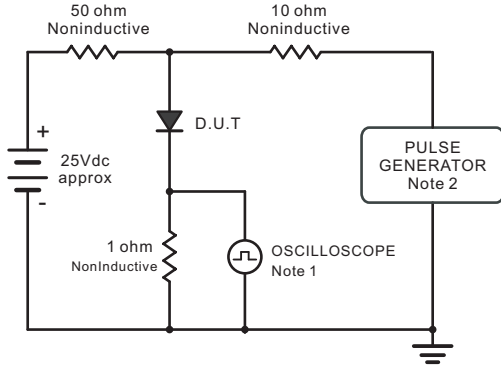
### ■外形尺寸和印记 Outline Dimensions and Mark



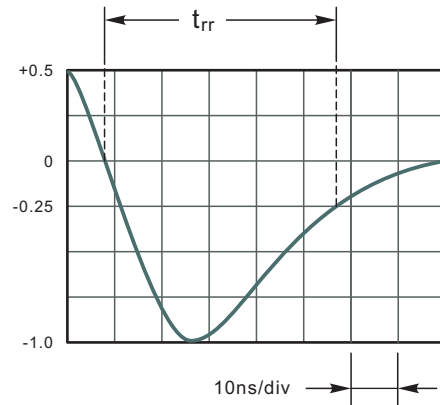
Parameter	Symbols	UMB1F	UMB2F	UMB4F	UMB6F	UMB8F	UMB10F	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	100	200	400	600	800	1000	V
Average Rectified Output Current at $T_c = 125^\circ\text{C}$	$I_o$	1.0						A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	$I_{FSM}$	35						A
Maximum Forward Voltage at 1.0 A	$V_F$	1.0	1.3	1.5			V	
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_a = 25^\circ\text{C}$ $T_a = 125^\circ\text{C}$	$I_R$	5.0			100			$\mu\text{A}$
Typical Junction Capacitance <sup>1)</sup>	$C_j$	18						pF
Maximum Reverse Recovery Time <sup>2)</sup>	$t_{rr}$	50			75			ns
Typical Thermal Resistance <sup>3)</sup>	$R_{\theta JA}$ $R_{\theta JC}$	72			20			$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150						$^\circ\text{C}$

## ■特性曲线（典型） Characteristics(Typical)

**Fig.1 Reverse Recovery Time Characteristic And Test Circuit Diagram**

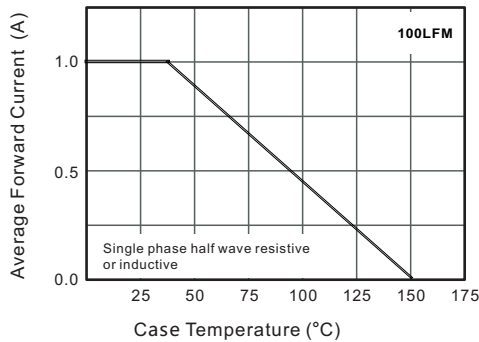


Note: 1. Rise Time = 7ns, max.  
Input Impedance = 1megohm, 22pF.  
2. Rises Time = 10ns, max.  
Source Impedance = 50 ohms.

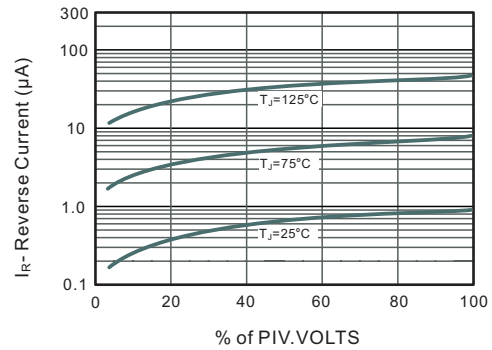


Set time Base for 10ns/div

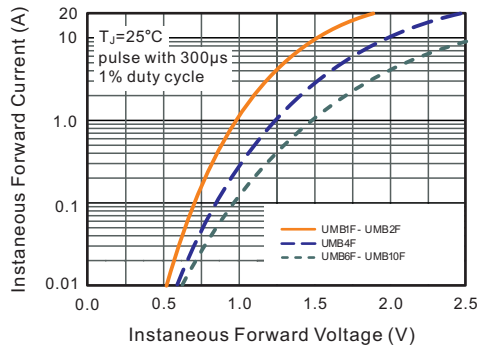
**Fig.2 Maximum Average Forward Current Rating**



**Fig.3 Typical Reverse Characteristics**



**Fig.3 Typical Instaneous Forward Characteristics**



**Fig.4 Maximum Non-Repetitive Peak Forward Surge Current**

